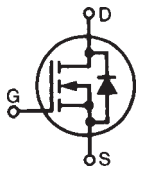
IXYS

PolarHT™ Power MOSFET

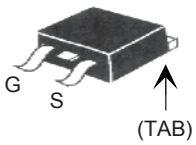
IXTA 62N15P
IXTP 62N15P
IXTQ 62N15P

V_{DSS} = 150 V
I_{D25} = 62 A
$R_{DS(on)}$ ≤ 40 mΩ

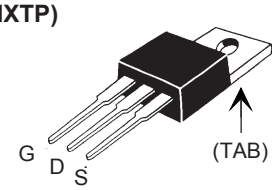
N-Channel Enhancement Mode
Avalanche Rated



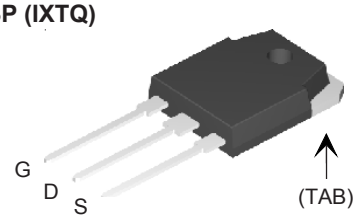
TO-263 (IXTA)



TO-220 (IXTP)



TO-3P (IXTQ)



G = Gate D = Drain
S = Source TAB = Drain

Symbol	Test Conditions	Maximum Ratings	
V_{DSS}	T_J = 25° C to 175° C	150	V
V_{DGR}	T_J = 25° C to 175° C; R_{GS} = 1 MΩ	150	V
V_{GS}	Continuous	±20	V
V_{GSM}	Transient	±30	V
I_{D25}	T_C = 25° C	62	A
I_{DM}	T_C = 25° C, pulse width limited by T_{JM}	150	A
I_{AR}	T_C = 25° C	50	A
E_{AR}	T_C = 25° C	30	mJ
E_{AS}	T_C = 25° C	1.0	J
dv/dt	$I_S \le I_{DM}$, di/dt ≤100 A/μs, $V_{DD} \le V_{DSS}$, T_J ≤150° C, R_G = 10 Ω	10	V/ns
P_D	T_C = 25° C	350	W
T_J		-55 ... +175	°C
T_{JM}		175	°C
T_{stg}		-55 ... +150	°C
T_L	1.6 mm (0.062 in.) from case for 10 s	300	°C
T_{SOLD}	Plastic body for 10 s	2600	°C
Md	Mounting torque (TO-3P / TO-220)	1.13/10	Nm/lb.in.
Weight	TO-3P	5.5	g
	TO-220	4	g
	TO-263	3	g

Symbol (T_J = 25° C, unless otherwise specified)	Test Conditions	Characteristic Values Min.	Typ.	Max.	
BV_{DSS}	V_{GS} = 0 V, I_D = 250 μA	150			V
$V_{GS(th)}$	$V_{DS} = V_{GS}$, I_D = 250μA	3.0		5.5	V
I_{GSS}	V_{GS} = ±20 V_{DC}, V_{DS} = 0			±100	nA
I_{DSS}	$V_{DS} = V_{DSS}$, V_{GS} = 0 V			25	μA
	T_J = 150° C			250	μA
$R_{DS(on)}$	V_{GS} = 10 V, I_D = 0.5 I_{D25} Pulse test, t ≤300 μs, duty cycle d ≤ 2 %		33	40	mΩ

Features

- International standard packages
- Unclamped Inductive Switching (UIS) rated
- Low package inductance
  - easy to drive and to protect

Advantages

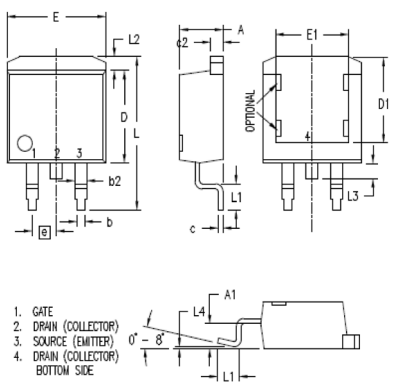
- Easy to mount
- Space savings
- High power density

Symbol	Test Conditions	Characteristic Values (T_J = 25°C, unless otherwise specified) Min.	Typ.	Max.	
g_{fs}	V_{DS}= 10 V; I_D = 0.5 I_{D25}, pulse test	14	24		S
C_{iss}	V_{GS} = 0 V, V_{DS} = 25 V, f = 1 MHz		2250		pF
C_{oss}			660		pF
C_{rss}			185		pF
$t_{d(on)}$	V_{GS} = 10 V, V_{DS} = 0.5 V_{DSS}, I_D = 0.5 I_{D25} R_G = 10 Ω (External)		27		ns
t_r			38		ns
$t_{d(off)}$			76		ns
t_f			35		ns
$Q_{g(on)}$	V_{GS}= 10 V, V_{DS} = 0.5 V_{DSS}, I_D = 0.5 I_{D25}		70		nC
Q_{gs}			20		nC
Q_{gd}			38		nC
R_{thJC}				0.42	°C/W
R_{thCS}	(TO-3P)		0.21		°C/W
	(TO-220)		0.25		°C/W

Source-Drain Diode

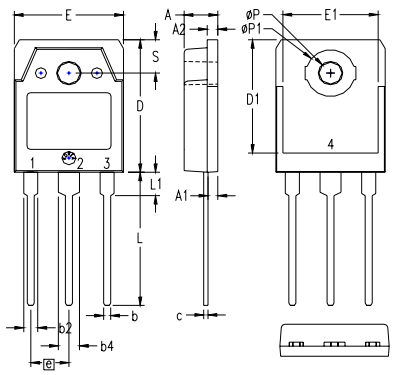
Symbol	Test Conditions	Characteristic Values (T_J = 25°C, unless otherwise specified) Min.	Typ.	Max.	
I_S	V_{GS} = 0 V			62	A
I_{SM}	Repetitive			150	A
V_{SD}	I_F = I_S, V_{GS} = 0 V, Pulse test, t ≤300 µs, duty cycle d≤ 2 %			1.5	V
t_{rr}	I_F = 25 A, -di/dt = 100 A/µs		150		ns
Q_{RM}	V_R = 100 V, V_{GS} = 0 V		2.0		µC

TO-263 (IXTA) Outline



SYM	INCHES MIN	INCHES MAX	MILLIMETERS MIN	MILLIMETERS MAX
A	.160	.190	4.06	4.83
A1	.080	.110	2.03	2.79
b	.020	.039	0.51	0.99
b2	.045	.055	1.14	1.40
c	.016	.029	0.40	0.74
c2	.045	.055	1.14	1.40
D	.340	.380	8.64	9.65
D1	.315	.350	8.00	8.89
E	.380	.410	9.65	10.41
E1	.245	.320	6.22	8.13
e	.100 BSC		2.54 BSC	
L	.575	.625	14.61	15.88
L1	.090	.110	2.29	2.79
L2	.040	.055	1.02	1.40
L3	.050	.070	1.27	1.78
L4	0	.005	0	0.13

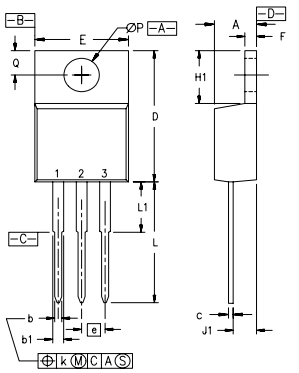
TO-3P (IXTQ) Outline



1 – GATE
2 – DRAIN (COLLECTOR)
3 – SOURCE (EMITTER)
4 – DRAIN (COLLECTOR)

SYM	INCHES MIN	INCHES MAX	MILLIMETERS MIN	MILLIMETERS MAX
A	.185	.193	4.70	4.90
A1	.051	.059	1.30	1.50
A2	.057	.065	1.45	1.65
b	.035	.045	0.90	1.15
b2	.075	.087	1.90	2.20
b4	.114	.126	2.90	3.20
c	.022	.031	0.55	0.80
D	.780	.799	19.80	20.30
D1	.665	.677	16.90	17.20
E	.610	.622	15.50	15.80
E1	.531	.539	13.50	13.70
e	.215 BSC		5.45 BSC	
L	.779	.795	19.80	20.20
L1	.134	.142	3.40	3.60
øP	.126	.134	3.20	3.40
øP1	.272	.280	6.90	7.10
S	.193	.201	4.90	5.10

TO-220 (IXTP) Outline



Pins: 1 - Gate 2 - Drain
3 - Source Tab - Drain

SYM	INCHES MIN	INCHES MAX	MILLIMETERS MIN	MILLIMETERS MAX
A	.170	.190	4.32	4.83
b	.025	.040	0.64	1.02
b1	.045	.065	1.15	1.65
c	.014	.022	0.35	0.56
D	.580	.630	14.73	16.00
E	.390	.420	9.91	10.66
e	.100 BSC		2.54 BSC	
F	.045	.055	1.14	1.40
H1	.230	.270	5.85	6.85
J1	.090	.110	2.29	2.79
k	0	.015	0	0.38
L	.500	.550	12.70	13.97
L1	.110	.230	2.79	5.84
ØP	.139	.161	3.53	4.08
Q	.100	.125	2.54	3.18

Fig. 1. Output Characteristics @ 25°C

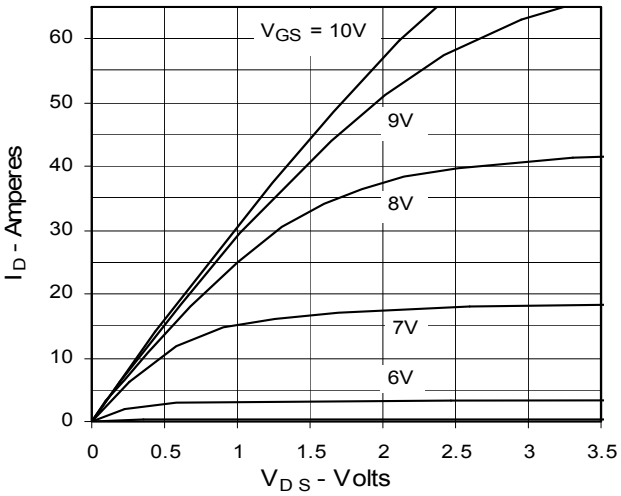


Fig. 2. Extended Output Characteristics @ 25°C

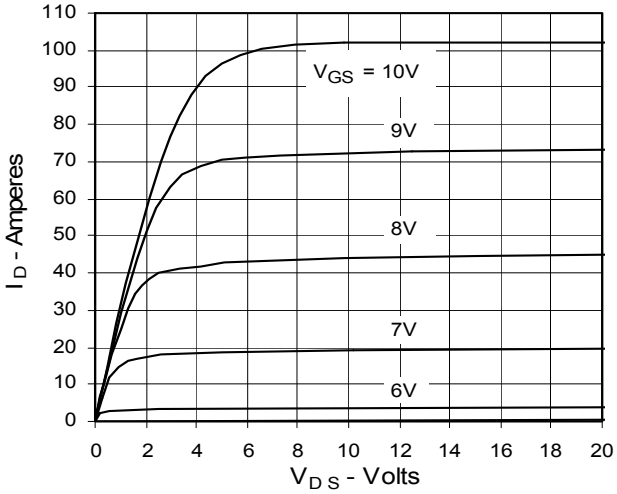


Fig. 3. Output Characteristics @ 150°C

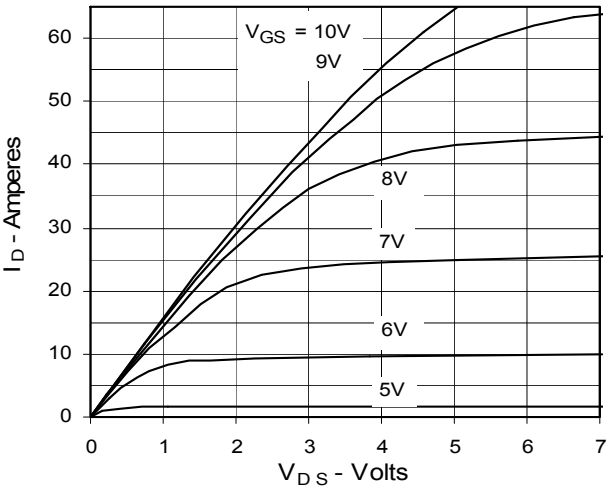


Fig. 4. $R_{DS(on)}$ Normalized to 0.5 I_{D25} Value vs. Junction Temperature

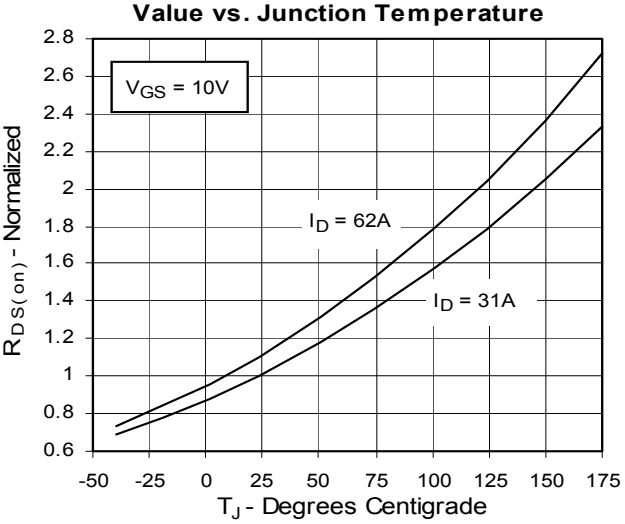


Fig. 5. $R_{DS(on)}$ Normalized to 0.5 I_{D25} Value vs. I_D

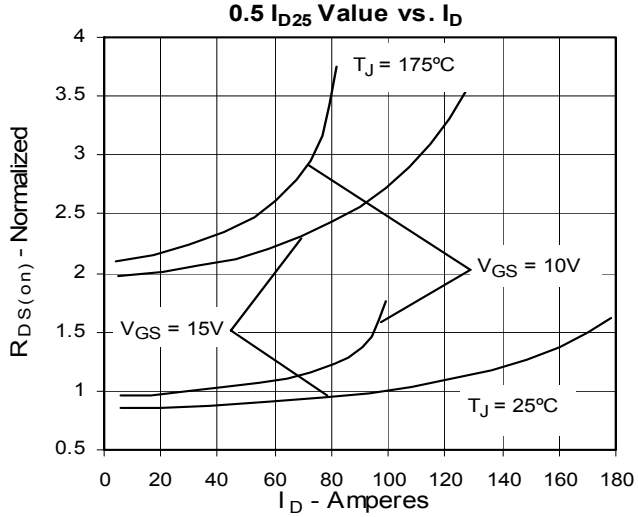


Fig. 6. Drain Current vs. Case Temperature

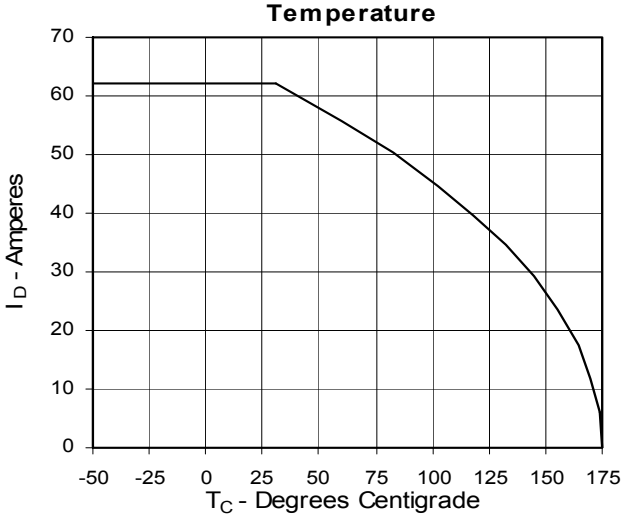


Fig. 7. Input Admittance

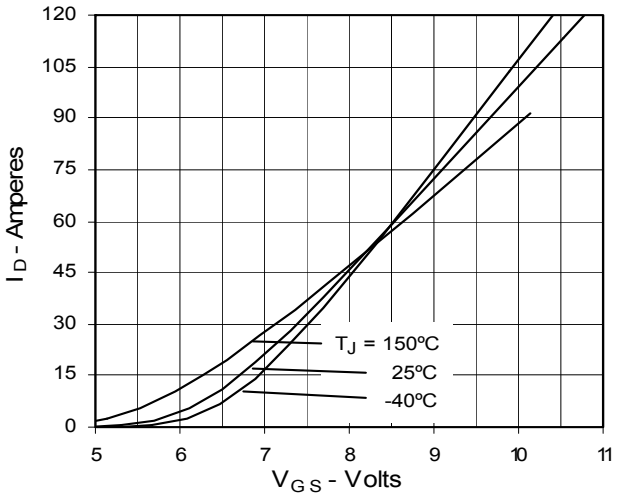


Fig. 8. Transconductance

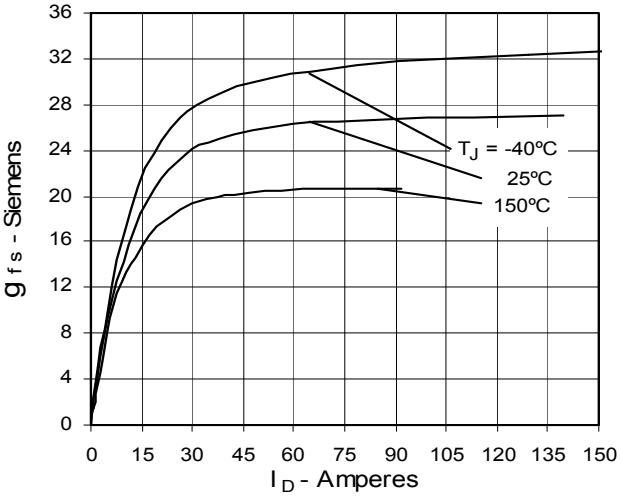


Fig. 9. Source Current vs. Source-To-Drain Voltage

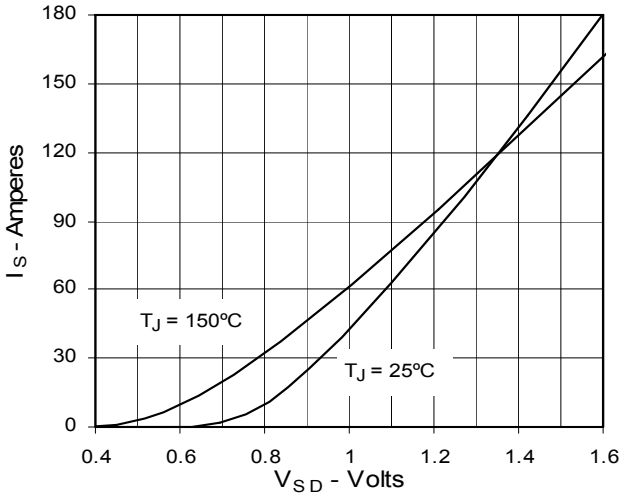


Fig. 10. Gate Charge

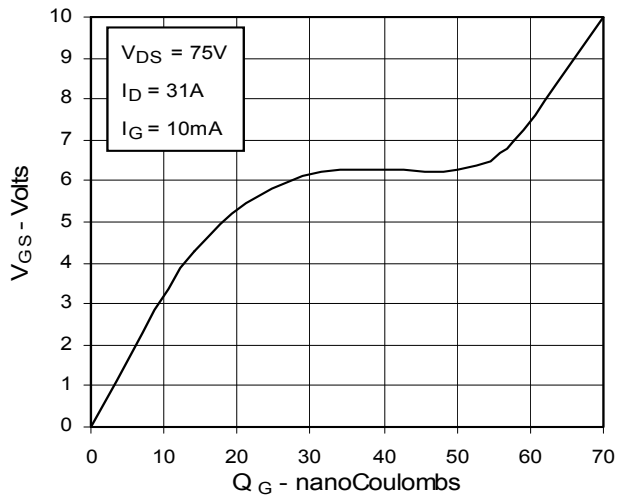


Fig. 11. Capacitance

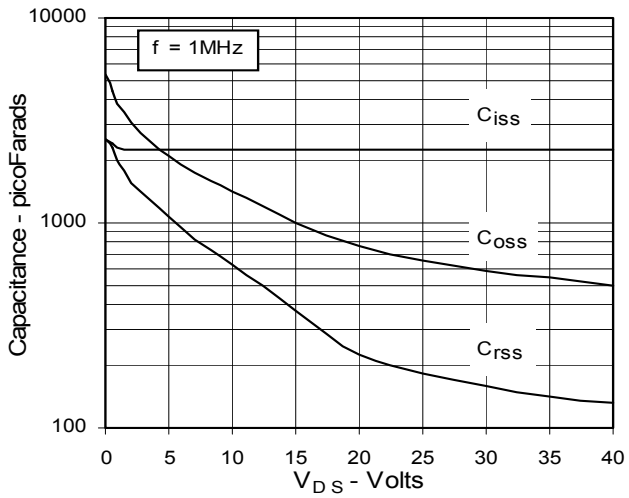


Fig. 12. Forward-Bias Safe Operating Area

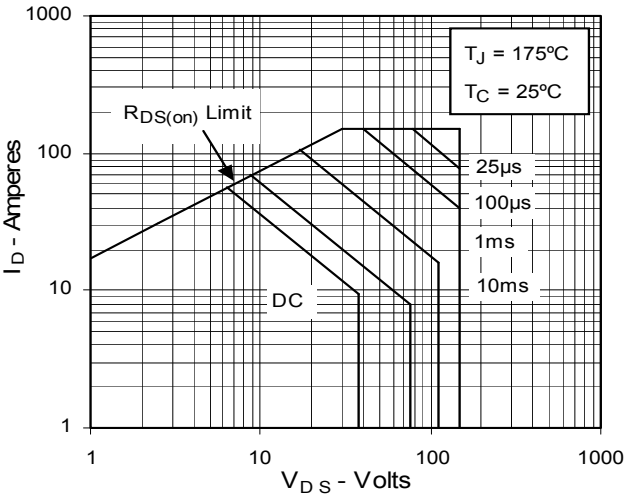


Fig. 13. Maximum Transient Thermal Resistance